



MCH3456

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		15	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		1.8	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	7.2	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm)	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	15			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =15V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1A	1.5	2.6		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1A, V _{GS} =4V		120	160	mΩ
	R _{DS(on)2}	I _D =0.5A, V _{GS} =2.5V		165	240	mΩ
	R _{DS(on)3}	I _D =0.1A, V _{GS} =1.8V		230	350	mΩ
	R _{DS(on)4}	I _D =0.1A, V _{GS} =1.5V		310	750	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		105		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		30		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		24		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7.8		ns
Rise Time	t _r	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		18		ns
Fall Time	t _f	See specified Test Circuit.		22		ns

Marking : LH

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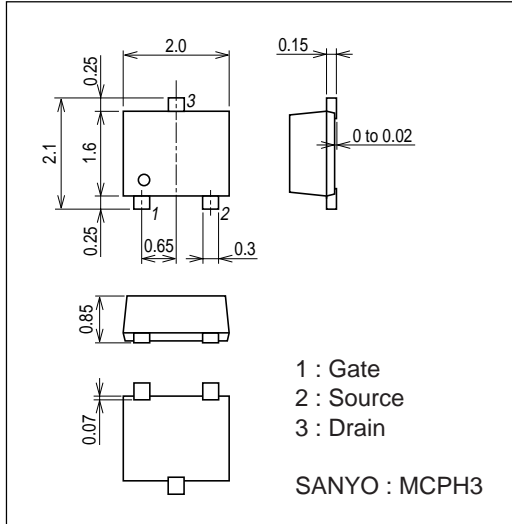
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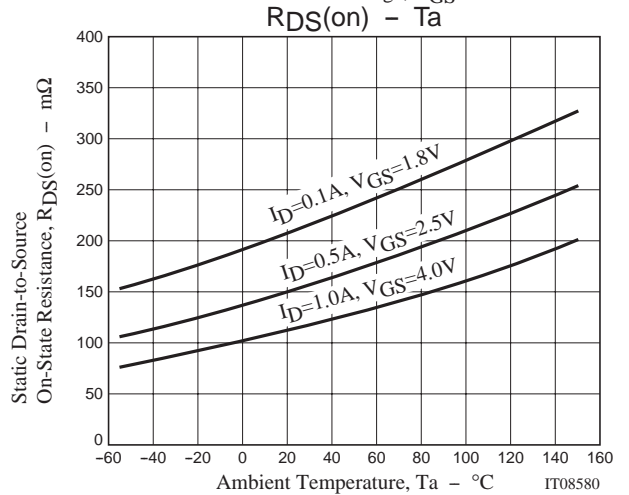
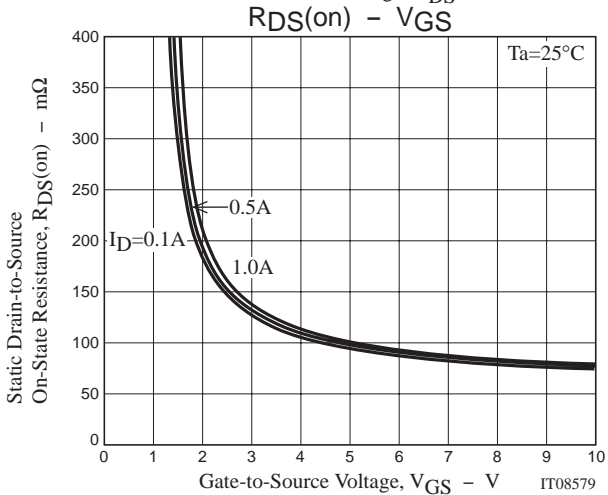
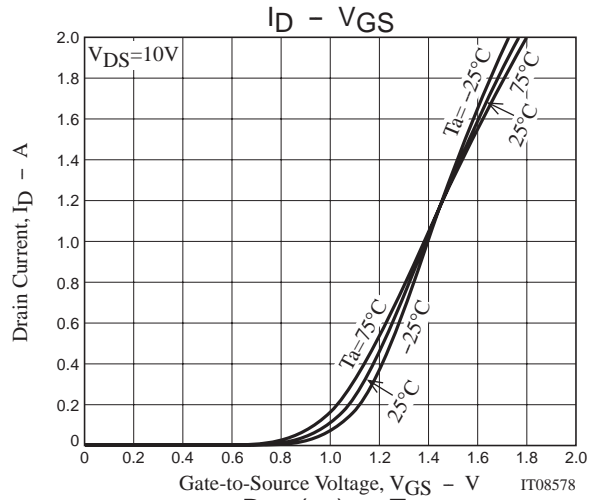
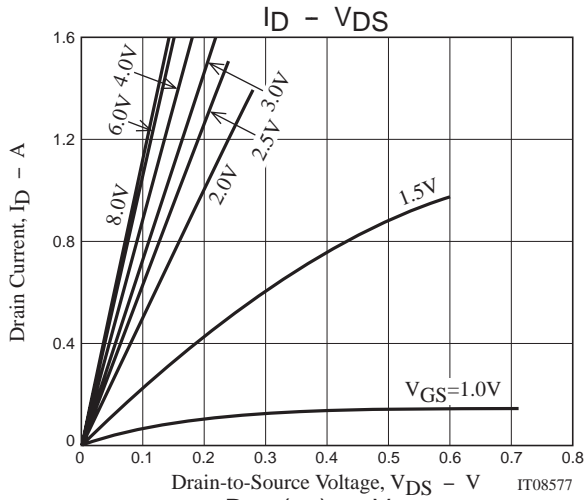
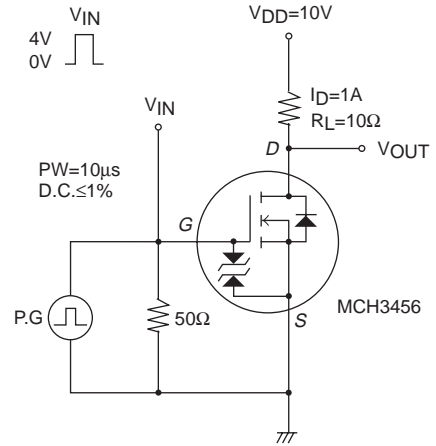
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =1.8A		1.86		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =1.8A		0.33		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =1.8A		0.55		nC
Diode Forward Voltage	V _{SD}	I _S =1.8A, V _{GS} =0V		0.88	1.2	V

Package Dimensions

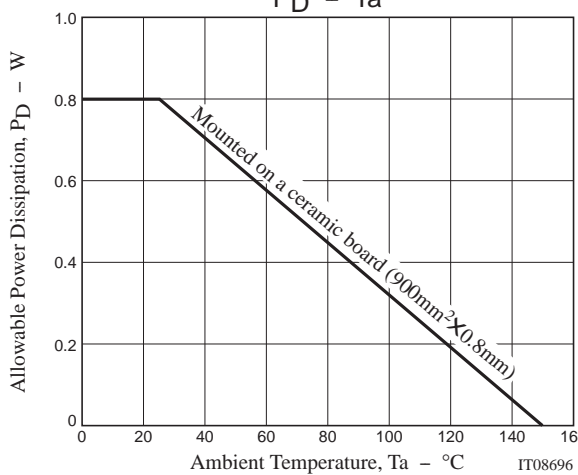
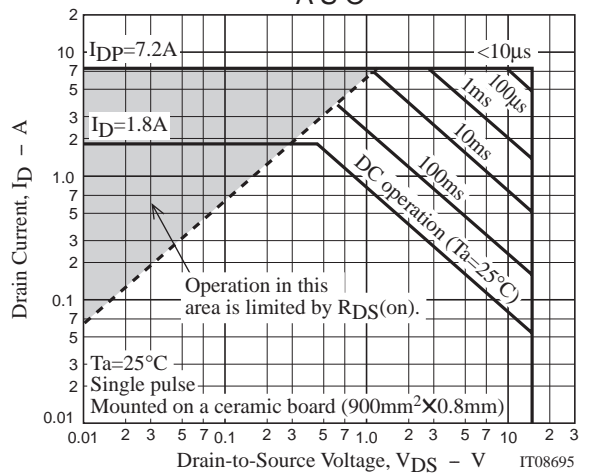
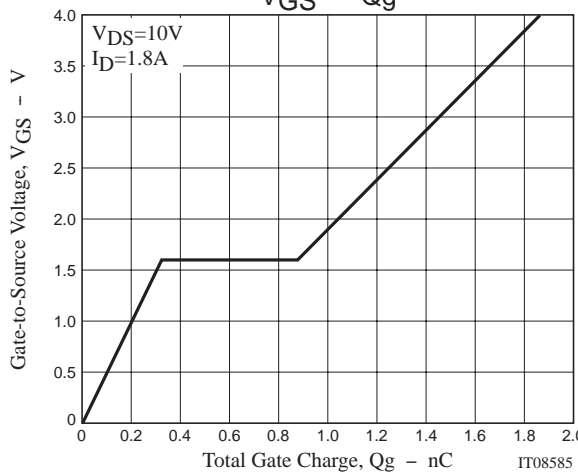
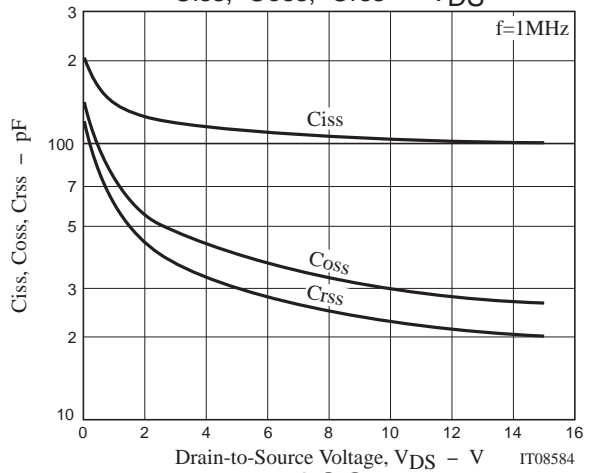
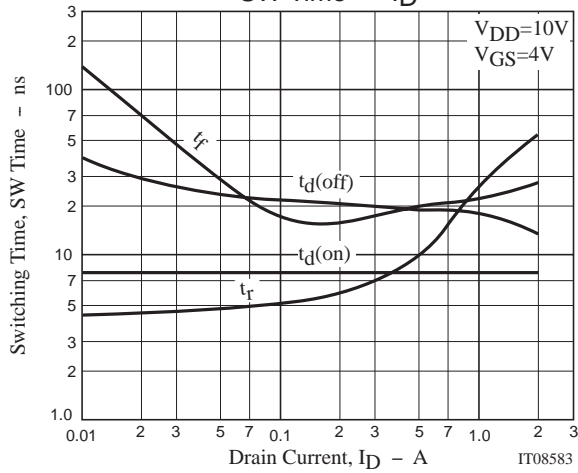
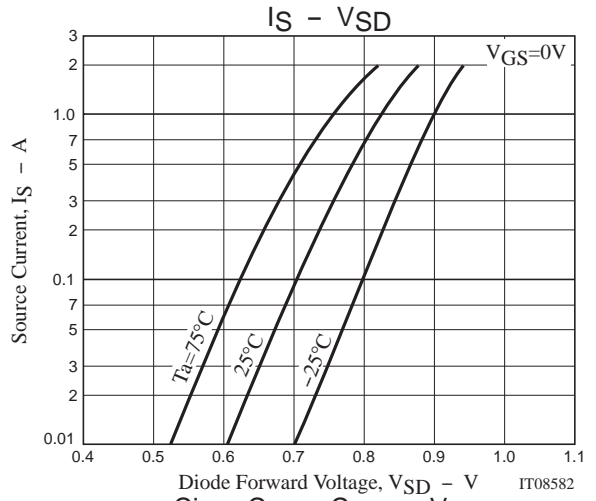
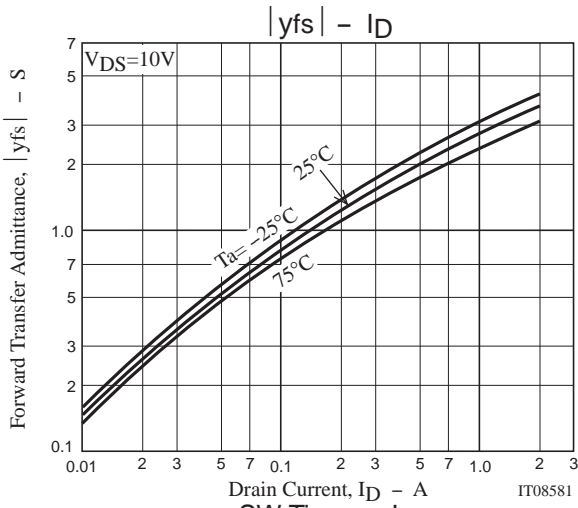
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Switching Time Test Circuit



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Note on usage : Since the MCH3456 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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